

NGB8202N, NGB8202AN

Ignition IGBT

20 A, 400 V, N-Channel D²PAK

This Logic Level Insulated Gate Bipolar Transistor (IGBT) features monolithic circuitry integrating ESD and Overvoltage clamped protection for use in inductive coil drivers applications. Primary uses include Ignition, Direct Fuel Injection, or wherever high voltage and high current switching is required.

Features

- Ideal for Coil-on-Plug and Driver-on-Coil Applications
- Gate-Emitter ESD Protection
- Temperature Compensated Gate-Collector Voltage Clamp Limits Stress Applied to Load
- Integrated ESD Diode Protection
- Low Threshold Voltage for Interfacing Power Loads to Logic or Microprocessor Devices
- Low Saturation Voltage
- High Pulsed Current Capability
- These are Pb-Free Devices

Applications

- Ignition Systems

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CES}	440	V
Collector-Gate Voltage	V _{CER}	440	V
Gate-Emitter Voltage	V _{GE}	± 15	V
Collector Current-Continuous @ T _C = 25°C - Pulsed	I _C	20 50	A _{DC} A _{AC}
Continuous Gate Current	I _G	1.0	mA
Transient Gate Current (t _s ≤ 2 ms, f ≤ 100 Hz)	I _G	20	mA
ESD (Charged-Device Model)	ESD	2.0	kV
ESD (Human Body Model) R = 1500 Ω, C = 100 pF	ESD	8.0	kV
ESD (Machine Model) R = 0 Ω, C = 200 pF	ESD	500	V
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	150 1.0	W W/°C
Operating & Storage Temperature Range	T _J , T _{stg}	-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

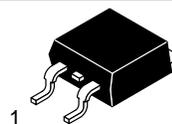
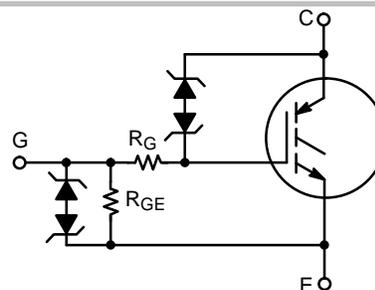


ON Semiconductor®

www.onsemi.com

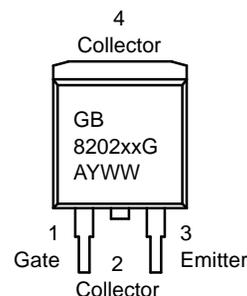
20 AMPS, 400 VOLTS

**V_{CE(on)} = 1.3 V @
I_C = 10 A, V_{GE} ≥ 4.5 V**



**D²PAK
CASE 418B
STYLE 4**

MARKING DIAGRAM



GB8202xx = Device Code
xx = N or AN
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NGB8202NT4G	D ² PAK (Pb-Free)	800/Tape & Reel
NGB8202ANT4G		
NGB8202ANTF4G		700/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NGB8202N, NGB8202AN

UNCLAMPED COLLECTOR-TO-EMITTER AVALANCHE CHARACTERISTICS ($-55^{\circ} \leq T_J \leq 175^{\circ} \text{C}$)

Characteristic	Symbol	Value	Unit
Single Pulse Collector-to-Emitter Avalanche Energy $V_{CC} = 50 \text{ V}$, $V_{GE} = 5.0 \text{ V}$, Pk $I_L = 16.7 \text{ A}$, $R_G = 1000 \Omega$, $L = 1.8 \text{ mH}$, Starting $T_J = 25^{\circ} \text{C}$ $V_{CC} = 50 \text{ V}$, $V_{GE} = 5.0 \text{ V}$, Pk $I_L = 14.9 \text{ A}$, $R_G = 1000 \Omega$, $L = 1.8 \text{ mH}$, Starting $T_J = 150^{\circ} \text{C}$ $V_{CC} = 50 \text{ V}$, $V_{GE} = 5.0 \text{ V}$, Pk $I_L = 14.1 \text{ A}$, $R_G = 1000 \Omega$, $L = 1.8 \text{ mH}$, Starting $T_J = 175^{\circ} \text{C}$	E_{AS}	250 200 180	mJ
Reverse Avalanche Energy $V_{CC} = 100 \text{ V}$, $V_{GE} = 20 \text{ V}$, Pk $I_L = 25.8 \text{ A}$, $L = 6.0 \text{ mH}$, Starting $T_J = 25^{\circ} \text{C}$	$E_{AS(R)}$	2000	mJ

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.0	$^{\circ} \text{C/W}$
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	62.5	$^{\circ} \text{C/W}$
Maximum Temperature for Soldering Purposes, 1/8" from case for 5 seconds (Note 2)	T_L	275	$^{\circ} \text{C}$

- When surface mounted to an FR4 board using the minimum recommended pad size.
- For further details, see Soldering and Mounting Techniques Reference Manual: SOLDERRM/D.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
----------------	--------	-----------------	-------------	-----	-----	-----	------

OFF CHARACTERISTICS

Collector-Emitter Clamp Voltage	BV_{CES}	$I_C = 2.0 \text{ mA}$	$T_J = -40^{\circ} \text{C to } 175^{\circ} \text{C}$	370	395	420	V	
		$I_C = 10 \text{ mA}$	$T_J = -40^{\circ} \text{C to } 175^{\circ} \text{C}$	390	415	440		
Zero Gate Voltage Collector Current	I_{CES}	$V_{GE} = 0 \text{ V}$, $V_{CE} = 15 \text{ V}$	$T_J = 25^{\circ} \text{C}$		0.1	1.0	μA	
			$T_J = 25^{\circ} \text{C}$	$V_{CE} = 200 \text{ V}$, $V_{GE} = 0 \text{ V}$	0.5	1.5	10	μA
					$T_J = 175^{\circ} \text{C}$	1.0	25	
Reverse Collector-Emitter Clamp Voltage	$BV_{CES(R)}$	$I_C = -75 \text{ mA}$	$T_J = 25^{\circ} \text{C}$	30	35	39	V	
			$T_J = 175^{\circ} \text{C}$	35	39	45*		
			$T_J = -40^{\circ} \text{C}$	30	33	37		
Reverse Collector-Emitter Leakage Current	$I_{CES(R)}$	$V_{CE} = -24 \text{ V}$ – NGB8202N	$T_J = 25^{\circ} \text{C}$	0.05	0.1	0.5	mA	
			$T_J = 175^{\circ} \text{C}$	1.0	5.0	10		
			$T_J = -40^{\circ} \text{C}$	0.005	0.01	0.1		
			$T_J = 25^{\circ} \text{C}$	0.05	0.2	1.0		
			$T_J = 175^{\circ} \text{C}$	1.0	8.5	25		
		$V_{CE} = -24 \text{ V}$ – NGB8202AN	$T_J = -40^{\circ} \text{C}$	0.005	0.025	0.2		
Gate-Emitter Clamp Voltage	BV_{GES}	$I_G = \pm 5.0 \text{ mA}$	$T_J = -40^{\circ} \text{C to } 175^{\circ} \text{C}$	12	12.5	14	V	
Gate-Emitter Leakage Current	I_{GES}	$V_{GE} = \pm 5.0 \text{ V}$	$T_J = -40^{\circ} \text{C to } 175^{\circ} \text{C}$	200	300	350*	μA	
Gate Resistor	R_G		$T_J = -40^{\circ} \text{C to } 175^{\circ} \text{C}$		70		Ω	
Gate-Emitter Resistor	R_{GE}		$T_J = -40^{\circ} \text{C to } 175^{\circ} \text{C}$	14.25	16	25	k Ω	

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	$V_{GE(th)}$	$I_C = 1.0 \text{ mA}$, $V_{GE} = V_{CE}$	$T_J = 25^{\circ} \text{C}$	1.5	1.8	2.1	V
			$T_J = 175^{\circ} \text{C}$	0.7	1.0	1.3	
			$T_J = -40^{\circ} \text{C}$	1.7	2.0	2.3*	
Threshold Temperature Coefficient (Negative)				4.0	4.6	5.2	mV/ $^{\circ} \text{C}$

*Maximum Value of Characteristic across Temperature Range.

- Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2\%$.

NGB8202N, NGB8202AN

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
----------------	--------	-----------------	-------------	-----	-----	-----	------

ON CHARACTERISTICS (Note 4)

Collector-to-Emitter On-Voltage	$V_{CE(on)}$	$I_C = 6.5 \text{ A}, V_{GE} = 3.7 \text{ V}$ - NGB8202N	$T_J = 25^\circ\text{C}$	0.95	1.15	1.35	V
			$T_J = 175^\circ\text{C}$	0.7	0.95	1.15	
			$T_J = -40^\circ\text{C}$	1.0	1.3	1.4	
		$I_C = 6.5 \text{ A}, V_{GE} = 3.7 \text{ V}$ - NGB8202AN	$T_J = 25^\circ\text{C}$	0.85	1.03	1.35	
			$T_J = 175^\circ\text{C}$	0.7	0.9	1.15	
			$T_J = -40^\circ\text{C}$	0.0	1.11	1.4	
		$I_C = 9.0 \text{ A}, V_{GE} = 3.9 \text{ V}$ - NGB8202N	$T_J = 25^\circ\text{C}$	0.95	1.25	1.45	
			$T_J = 175^\circ\text{C}$	0.8	1.05	1.25	
			$T_J = -40^\circ\text{C}$	1.1	1.4	1.5	
		$I_C = 9.0 \text{ A}, V_{GE} = 3.9 \text{ V}$ - NGB8202AN	$T_J = 25^\circ\text{C}$	0.9	1.11	1.45	
			$T_J = 175^\circ\text{C}$	0.8	1.01	1.25	
			$T_J = -40^\circ\text{C}$	1.0	1.18	1.5	
		$I_C = 7.5 \text{ A},$ $V_{GE} = 4.5 \text{ V}$	$T_J = 25^\circ\text{C}$	0.85	1.15	1.4	
			$T_J = 175^\circ\text{C}$	0.7	0.95	1.2	
			$T_J = -40^\circ\text{C}$	1.0	1.3	1.6*	
		$I_C = 10 \text{ A},$ $V_{GE} = 4.5 \text{ V}$	$T_J = 25^\circ\text{C}$	1.0	1.3	1.6	
			$T_J = 175^\circ\text{C}$	0.8	1.05	1.4	
			$T_J = -40^\circ\text{C}$	1.1	1.4	1.7*	
		$I_C = 15 \text{ A},$ $V_{GE} = 4.5 \text{ V}$	$T_J = 25^\circ\text{C}$	1.15	1.45	1.7	
			$T_J = 175^\circ\text{C}$	1.0	1.3	1.55	
			$T_J = -40^\circ\text{C}$	1.25	1.55	1.8*	
$I_C = 20 \text{ A}, V_{GE} = 4.5 \text{ V}$ - NGB8202N	$T_J = 25^\circ\text{C}$	1.3	1.6	1.9			
	$T_J = 175^\circ\text{C}$	1.2	1.5	1.8			
	$T_J = -40^\circ\text{C}$	1.4	1.75	2.0			
$I_C = 20 \text{ A}, V_{GE} = 4.5 \text{ V}$ - NGB8202AN	$T_J = 25^\circ\text{C}$	1.1	1.4	1.9			
	$T_J = 175^\circ\text{C}$	1.2	1.5	1.8			
	$T_J = -40^\circ\text{C}$	1.3	1.42	2.0			
Forward Transconductance	gfs	$I_C = 6.0 \text{ A},$ $V_{CE} = 5.0 \text{ V}$	$T_J = 25^\circ\text{C}$	10	18	25	Mhos

DYNAMIC CHARACTERISTICS

Input Capacitance	C_{ISS}	$f = 10 \text{ kHz}, V_{CE} = 25 \text{ V}$	$T_J = 25^\circ\text{C}$	1100	1300	1500	pF
Output Capacitance	C_{OSS}			70	80	90	
Transfer Capacitance	C_{RSS}			18	20	22	

NGB8202N, NGB8202AN

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Test Conditions	Temperature	Min	Typ	Max	Unit
----------------	--------	-----------------	-------------	-----	-----	-----	------

SWITCHING CHARACTERISTICS

Turn-Off Delay Time (Resistive)	$t_{d(off)}$	$V_{CC} = 300\text{ V}, I_C = 9.0\text{ A}$ $R_G = 1.0\text{ k}\Omega, R_L = 33\ \Omega,$ $V_{GE} = 5.0\text{ V}$	$T_J = 25^\circ\text{C}$	6.0	8.0	10	μSec
			$T_J = 175^\circ\text{C}$	6.0	8.0	10	
Fall Time (Resistive)	t_f		$T_J = 25^\circ\text{C}$	4.0	6.0	8.0	
			$T_J = 175^\circ\text{C}$	8.0	10.5	14	
Turn-Off Delay Time (Inductive)	$t_{d(off)}$	$V_{CC} = 300\text{ V}, I_C = 9.0\text{ A}$ $R_G = 1.0\text{ k}\Omega,$ $L = 300\ \mu\text{H}, V_{GE} = 5.0\text{ V}$	$T_J = 25^\circ\text{C}$	3.0	5.0	7.0	
			$T_J = 175^\circ\text{C}$	5.0	7.0	9.0	
Fall Time (Inductive)	t_f		$T_J = 25^\circ\text{C}$	1.5	3.0	4.5	
			$T_J = 175^\circ\text{C}$	5.0	7.0	10	
Turn-On Delay Time	$t_{d(on)}$		$V_{CC} = 14\text{ V}, I_C = 9.0\text{ A}$ $R_G = 1.0\text{ k}\Omega, R_L = 1.5\ \Omega,$ $V_{GE} = 5.0\text{ V}$	$T_J = 25^\circ\text{C}$	1.0	1.5	2.0
				$T_J = 175^\circ\text{C}$	1.0	1.5	2.0
Rise Time	t_r	$T_J = 25^\circ\text{C}$		4.0	6.0	8.0	
		$T_J = 175^\circ\text{C}$		3.0	5.0	7.0	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

*Maximum Value of Characteristic across Temperature Range.

4. Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

NGB8202N, NGB8202AN

TYPICAL ELECTRICAL CHARACTERISTICS

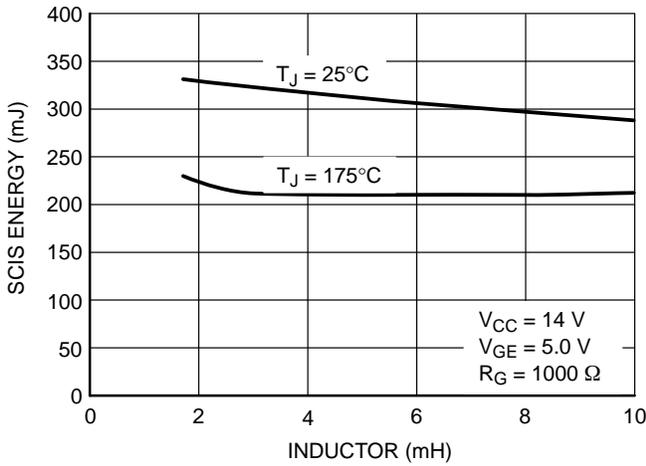


Figure 1. Self Clamped Inductive Switching

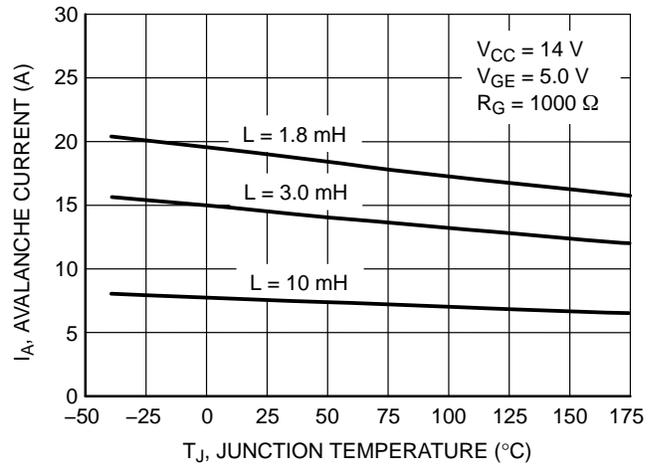


Figure 2. Open Secondary Avalanche Current vs. Temperature

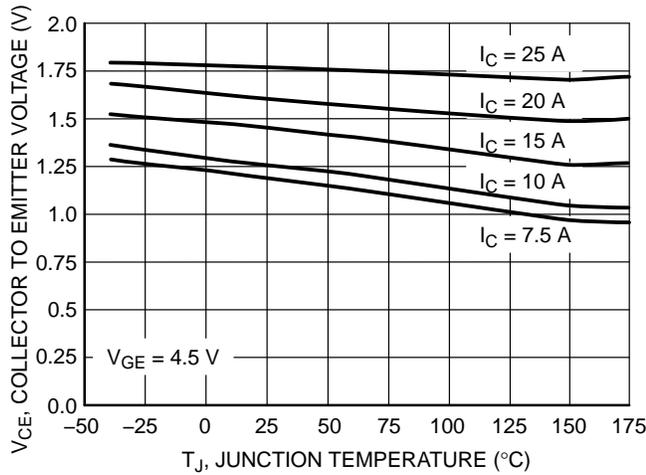


Figure 3. Collector-to-Emitter Voltage vs. Junction Temperature

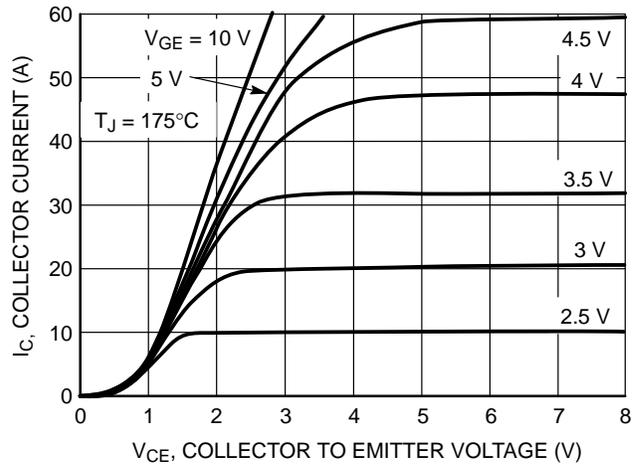


Figure 4. Collector Current vs. Collector-to-Emitter Voltage

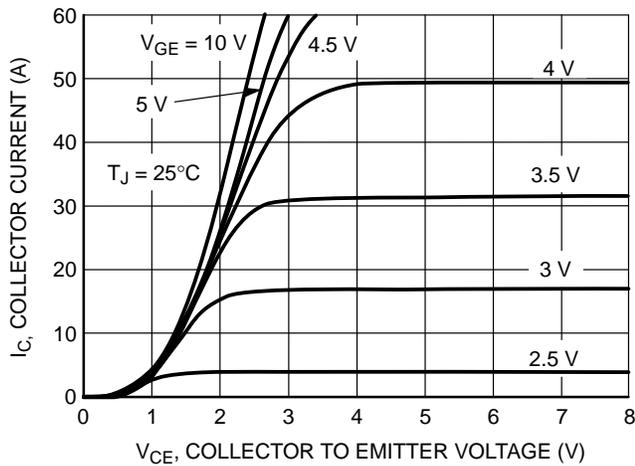


Figure 5. Collector Current vs. Collector-to-Emitter Voltage

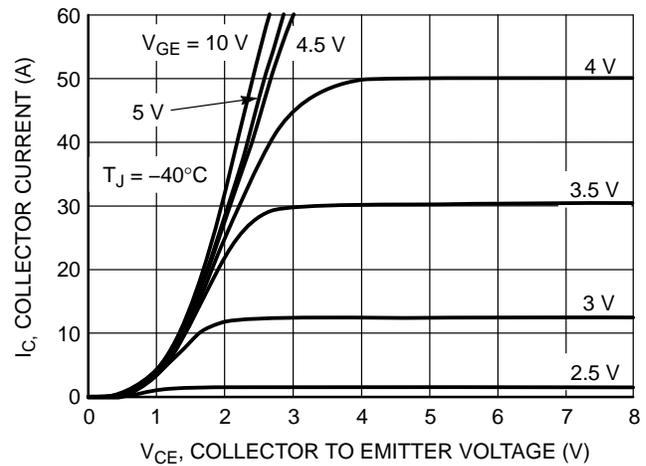


Figure 6. Collector Current vs. Collector-to-Emitter Voltage

TYPICAL ELECTRICAL CHARACTERISTICS

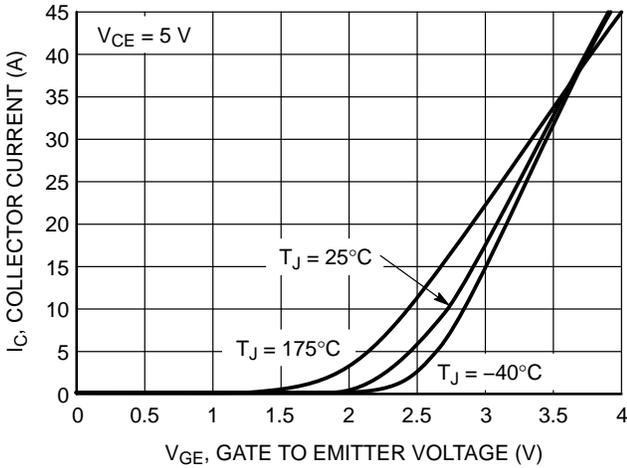


Figure 7. Transfer Characteristics

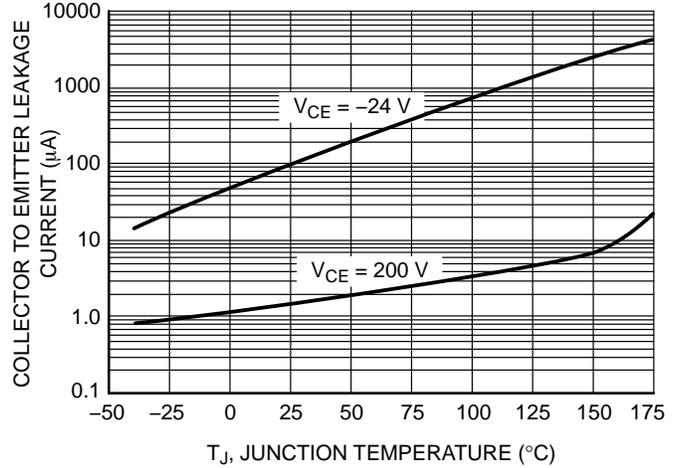


Figure 8. Collector-to-Emitter Leakage Current vs. Temperature

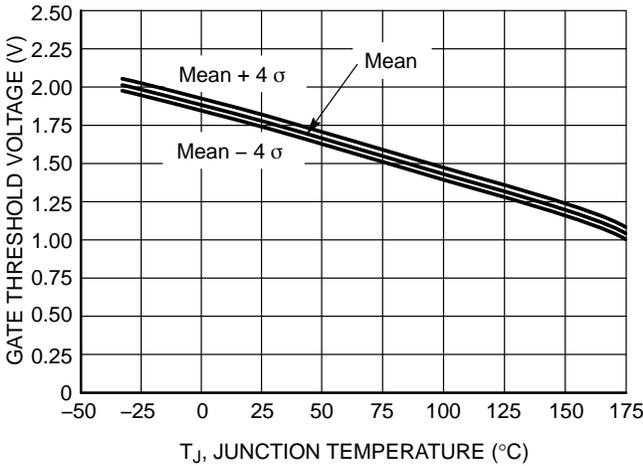


Figure 9. Gate Threshold Voltage vs. Temperature

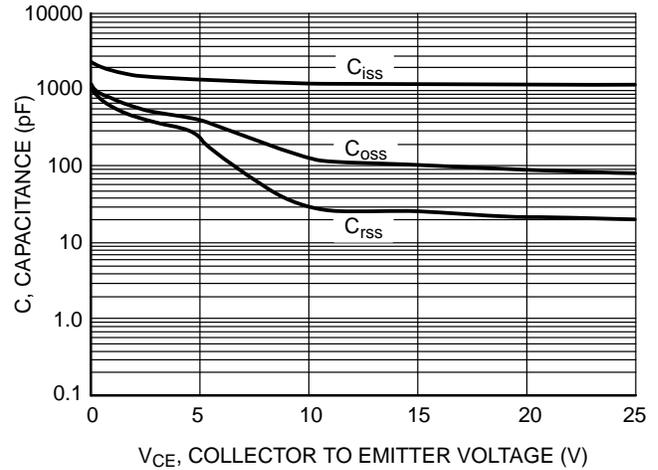


Figure 10. Capacitance vs. Collector-to-Emitter Voltage

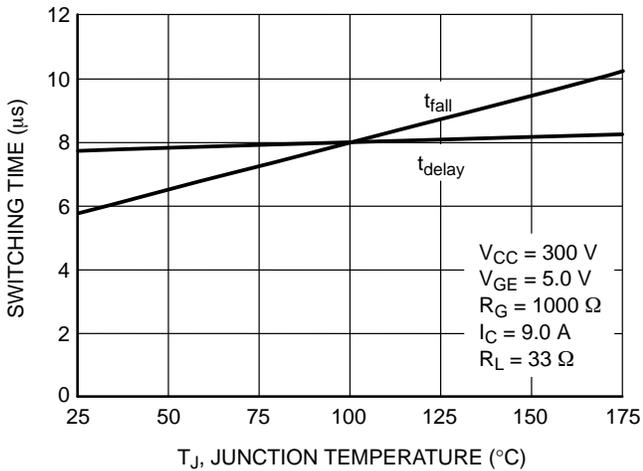


Figure 11. Resistive Switching Fall Time vs. Temperature

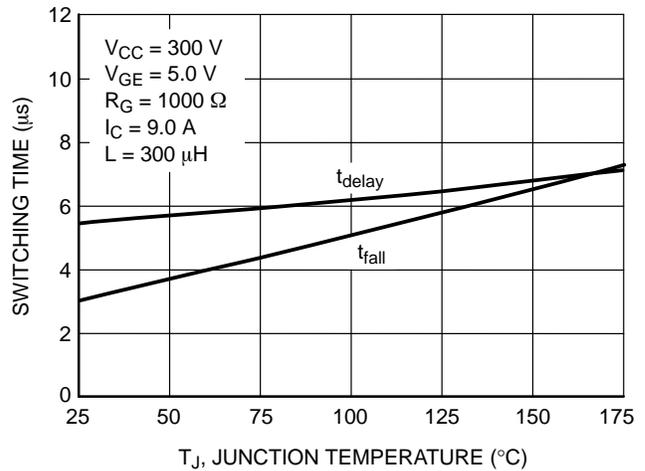
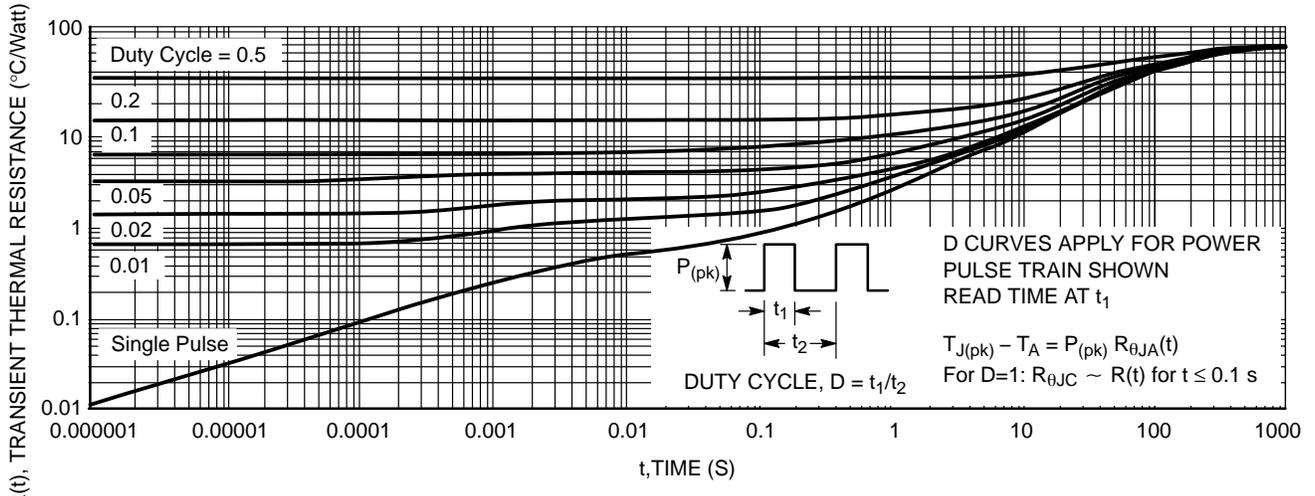
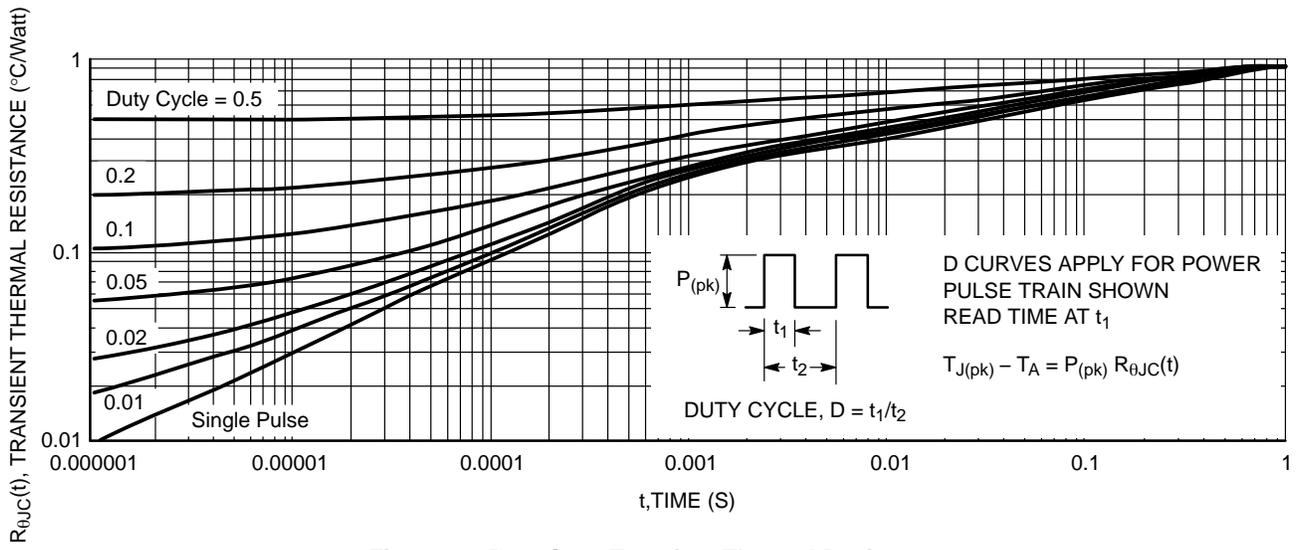


Figure 12. Inductive Switching Fall Time vs. Temperature

NGB8202N, NGB8202AN



**Figure 13. Minimum Pad Transient Thermal Resistance
(Non-normalized Junction-to-Ambient)**

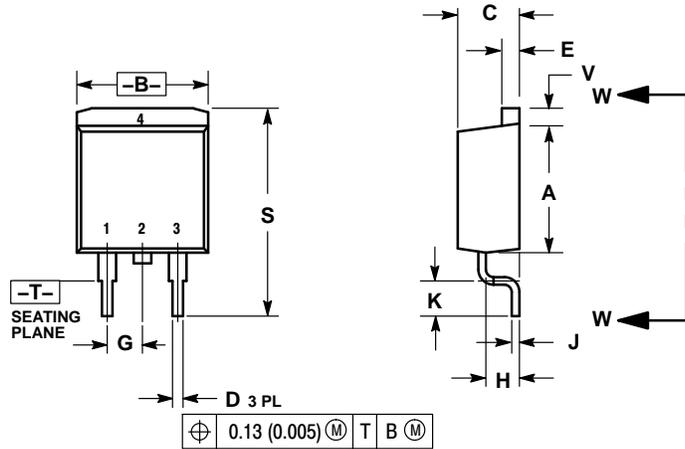


**Figure 14. Best Case Transient Thermal Resistance
(Non-normalized Junction-to-Case Mounted on Cold Plate)**

NGB8202N, NGB8202AN

PACKAGE DIMENSIONS

D²PAK 3 CASE 418B-04 ISSUE L

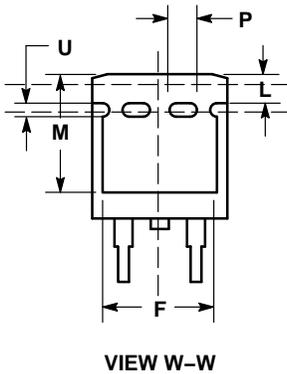


- NOTES:
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 - CONTROLLING DIMENSION: INCH.
 - 418B-01 THRU 418B-03 OBSOLETE, NEW STANDARD 418B-04.

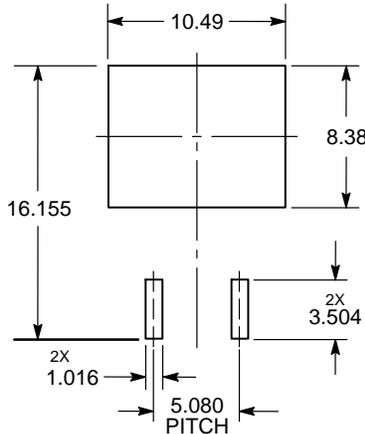
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.340	0.380	8.64	9.65
B	0.380	0.405	9.65	10.29
C	0.160	0.190	4.06	4.83
D	0.020	0.035	0.51	0.89
E	0.045	0.055	1.14	1.40
F	0.310	0.350	7.87	8.89
G	0.100 BSC		2.54 BSC	
H	0.080	0.110	2.03	2.79
J	0.018	0.025	0.46	0.64
K	0.090	0.110	2.29	2.79
L	0.052	0.072	1.32	1.83
M	0.280	0.320	7.11	8.13
N	0.197 REF		5.00 REF	
P	0.079 REF		2.00 REF	
R	0.039 REF		0.99 REF	
S	0.575	0.625	14.60	15.88
V	0.045	0.055	1.14	1.40

STYLE 4:

- PIN 1. GATE
- COLLECTOR
- EMITTER
- COLLECTOR



SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marketing.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free
USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: <http://www.onsemi.com/orderlit>

For additional information, please contact your local Sales Representative